MT8255N3

N-Channel Enhancement Mode Field Effect Transistor

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Product Summary

- V_{DS} = 20V
- I_D = 50A
- $R_{DS(ON)}$ = 3.5mΩ@V_{GS}=4.5V
- $R_{DS(ON)}$ = 4.5mΩ@V_{GS}=2.5V

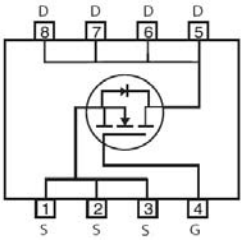
Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Applications

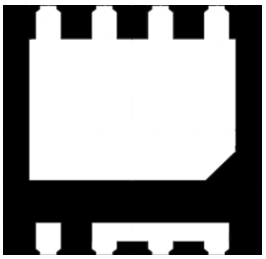
- Power switching application
- Load switching
- Uninterruptible power supply

Simplified Schematic



MARKING DIAGRAM & PIN ASSIGNMENT

DFN3X3-8L



PIN1

Absolute Maximum Ratings T_A=25℃ unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current [AF]	T_A=25℃	I_{DSM}	50	A
	T_A=70℃		45	
Pulsed Drain Current [B]		I_{DM}	160	A
Avalanche Current [C]		I_{AR}	55	A
Repetitive avalanche energy L=0.3mH [C]		E_{AR}	90	mJ
Power Dissipation	T_A=25℃	P_{DSM}	3.5	W
	T_A=70℃		1.8	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	32	40	℃/W
Maximum Junction-to-Ambient [A]	Steady-State		60	75	℃/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	16	24	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250uA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V			1	uA
		T_J=85℃			100	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±12V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	0.5	0.75	1.2	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	50			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=20A		3.5		mΩ
		V_{GS}=2.5V, I_D=18A		4.5		Ω
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		100		S
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_S=40A			1.2	V
I_S	Maximum Body-Diode + Schottky Continuous Current		55			A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		3000		pF
C_{oss}	Output Capacitance			700		pF
C_{rss}	Reverse Transfer Capacitance			390		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		0.8	1.2	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A		39	45	nC
Q_g(4.5V)	Total Gate Charge			30.4		nC
Q_{gs}	Gate Source Charge			9.5		nC
Q_{gd}	Gate Drain Charge			19.8		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1.2Ω, R_{GEN}=3Ω		12.5		ns
t_r	Turn-On Rise Time			35.5		ns
$t_{D(off)}$	Turn-Off DelayTime			40		ns
t_f	Turn-Off Fall Time			32.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=500A/ μs		15	17	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=500A/ μs		32	38	nC

A: The value of $R_{\theta JA}$ is measured withthe device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25℃. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25℃. The SOA curve provides a single pulse rating.

F. The current rating is based on the t ≤ 10s thermal resistance rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

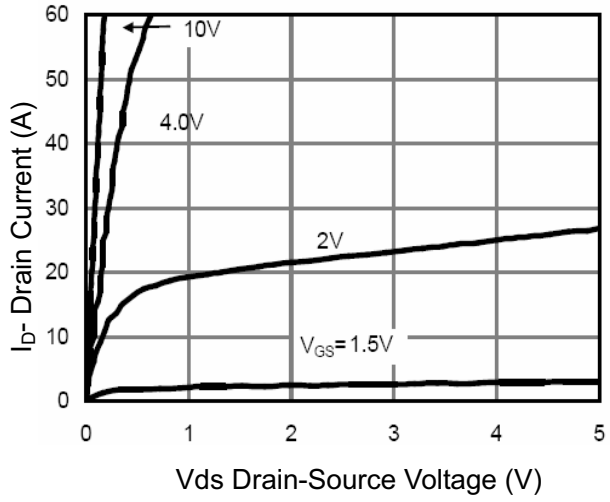


Figure 1 Output Characteristics

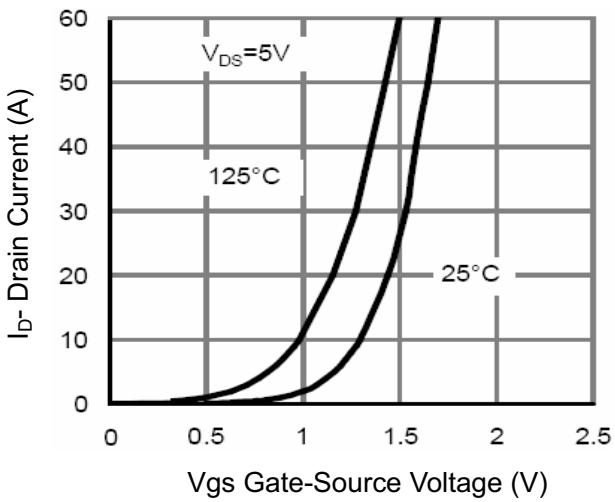


Figure 2 Transfer Characteristics

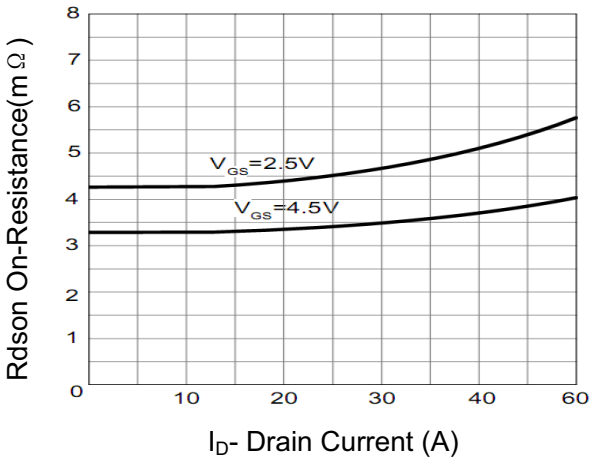


Figure 3 Rdson- Drain Current

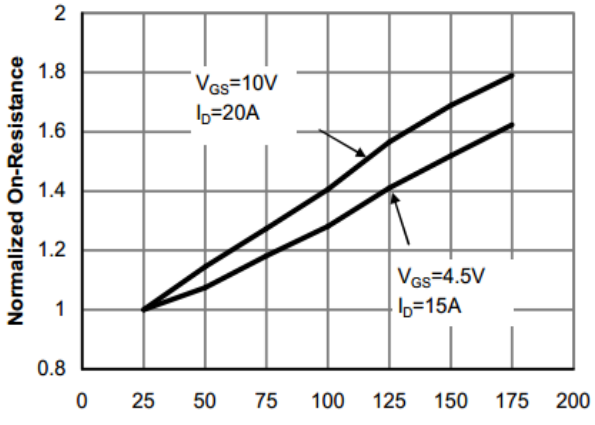


Figure 4: On-Resistance vs. Junction Temperature (Note E)

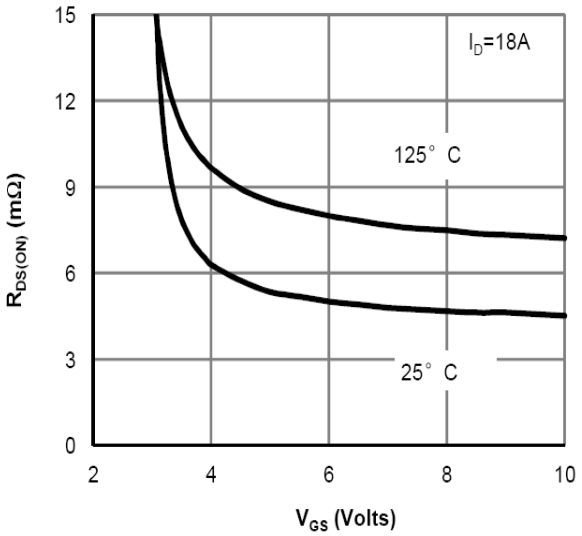


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

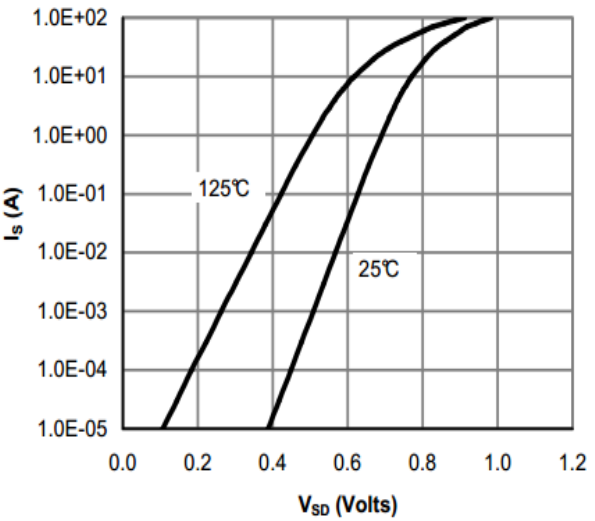


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

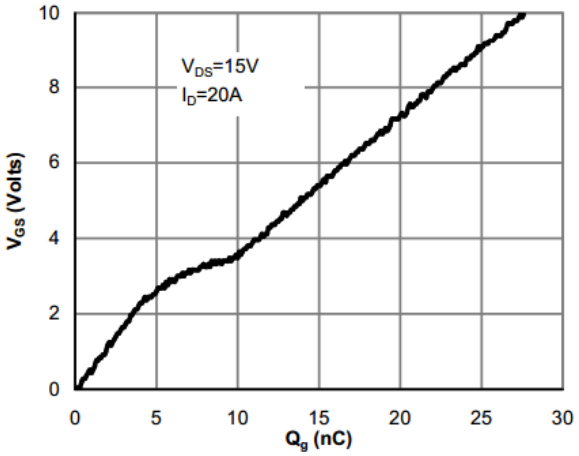


Figure 7: Gate-Charge Characteristics

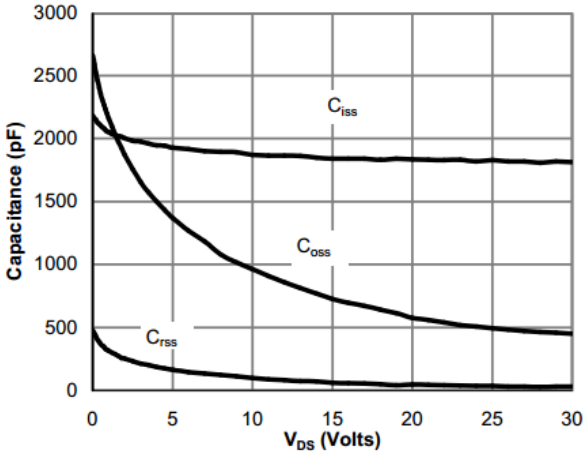


Figure 8: Capacitance Characteristics

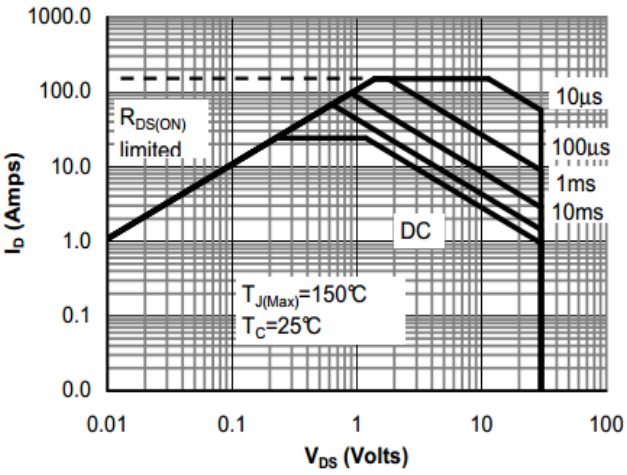


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

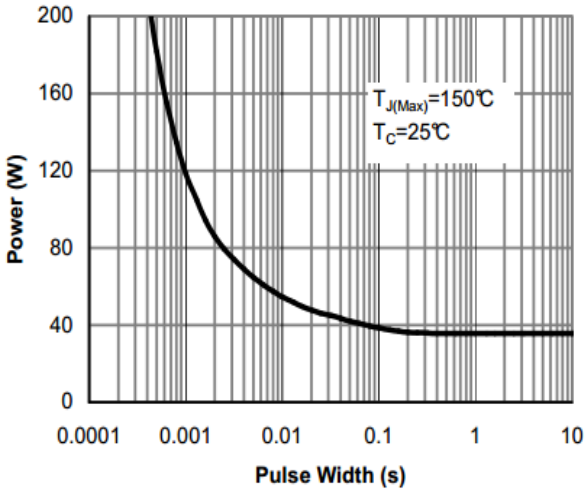


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

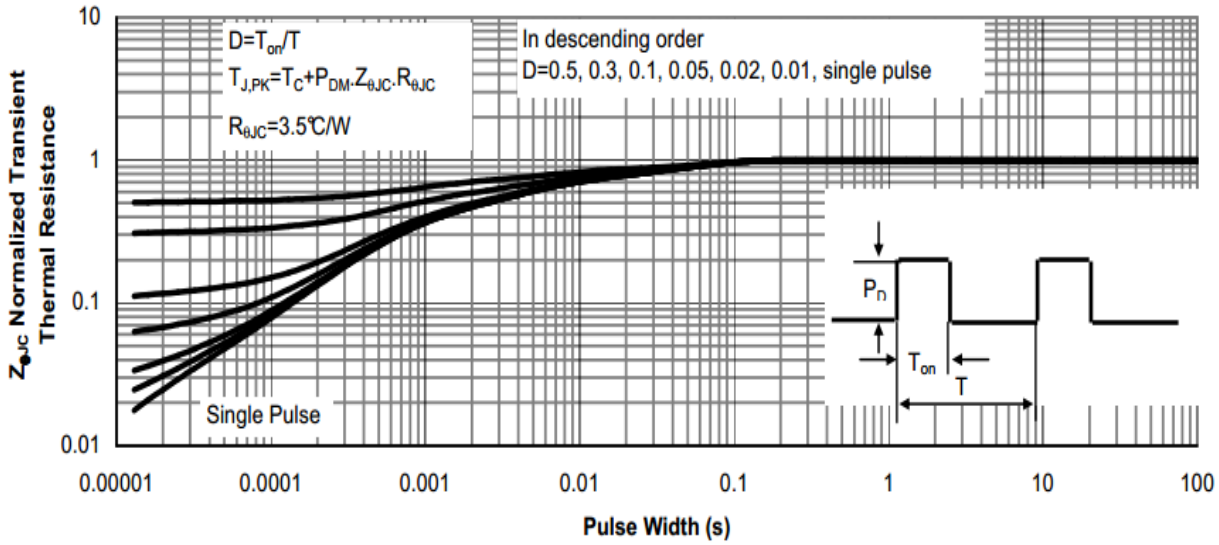
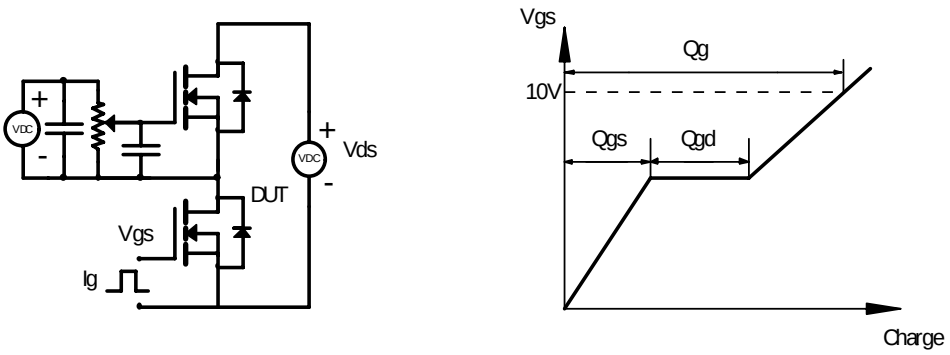
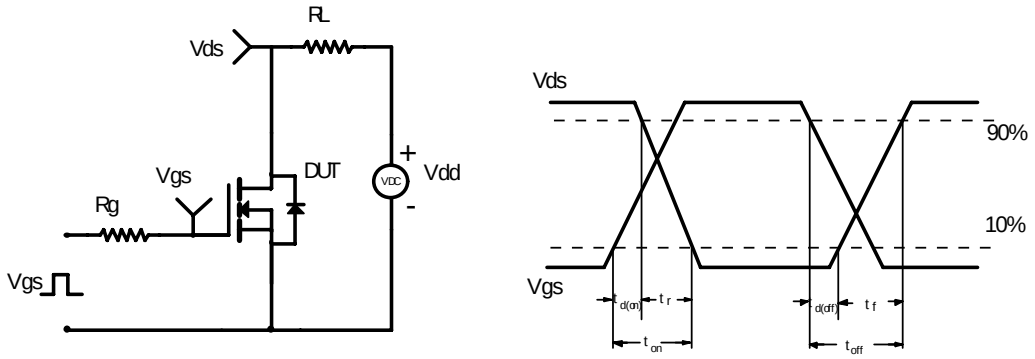


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

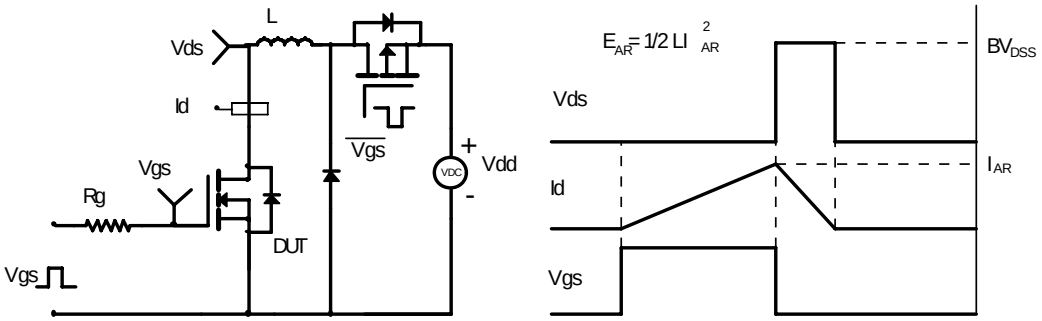
Gate Charge Test Circuit & Waveform



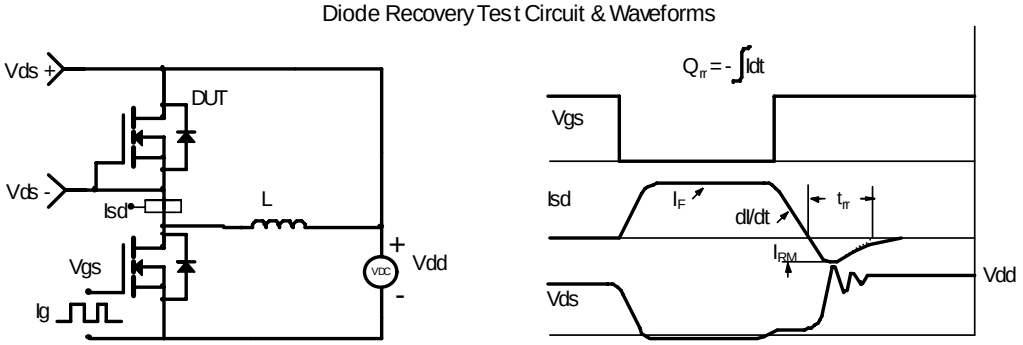
Resistive Switching Test Circuit & Waveforms



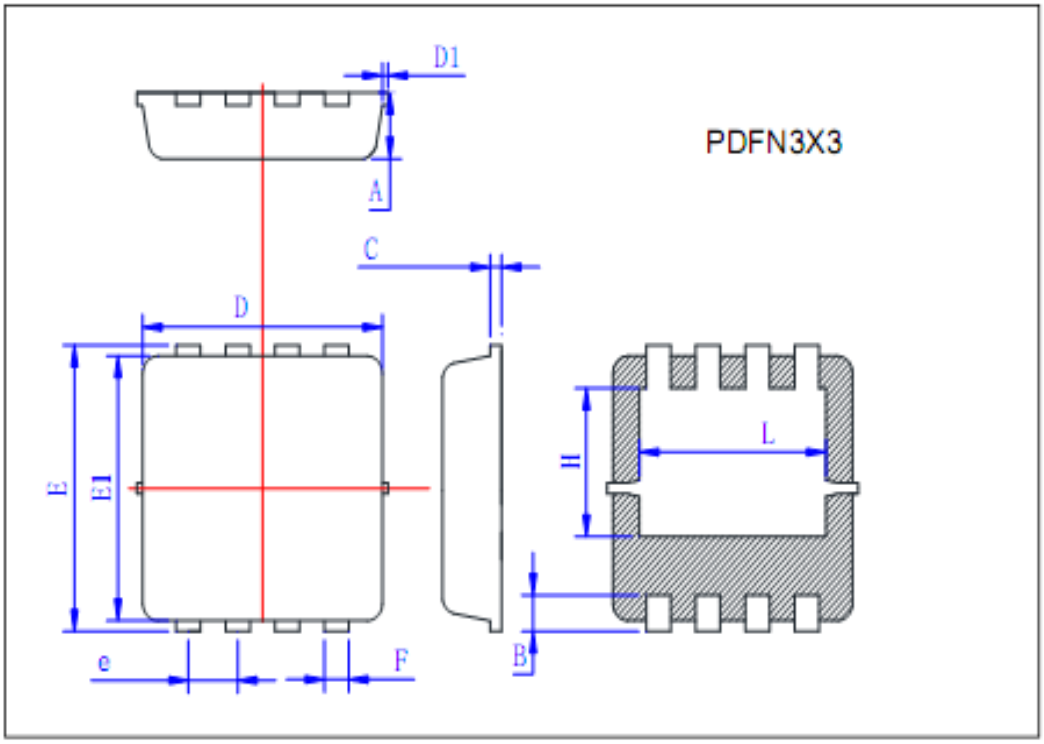
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



PACKAGE OUTLINE DIMENSIONS



Symbol	Min	Typ	Max
A	0.725	0.775	0.825
B	0.28	0.38	0.48
C	0.13	0.15	0.20
D	3.05	3.15	3.25
D1			0.10
E	3.25	3.35	3.45
E1	3.0	3.1	3.2
e	0.60	0.65	0.70
F	0.27	0.32	0.37
H	1.63	1.73	1.83
L	2.35	2.45	2.55

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